

Description

The SPD30P06PG uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO252-2L

General Features

 $V_{DS} = -60V I_{D} = -15 A$

 $R_{DS(ON)}$ < $82m\Omega$ @ V_{GS} =10V

Application

Battery protection

P-Channel MOSFET

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
SPD30P06PG	TO252-2L	30P06P XXXX	2500

Absolute Maximum Ratings (T_A=25[°]Cunless otherwise noted)

Symbol	ol Parameter Rati		Units	
V _{DS}	Drain-Source Voltage	-60	V	
V _G s	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-15	Α	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ¹	-11	Α	
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	t, V _{GS} @ -10V ¹ -4.3		
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ -10V ¹	-3.5	А	
Ірм	Pulsed Drain Current ²	-36	А	
EAS	Single Pulse Avalanche Energy ³	35.4	mJ	
las	Avalanche Current	-26.6	Α	
P _D @T _C =25°C	Total Power Dissipation ⁴	34.7	W	
P _D @T _A =25°C	Total Power Dissipation ⁴	2	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
R _θ JA	Thermal Resistance Junction-Ambient ¹	62	°C/W	
Rejc	Thermal Resistance Junction-Case ¹	3.6	°C/W	



Electrical Characteristics (T_A=25°Cunless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V
△Bvbss /△Tj	BV _{DSS} Temperature Coefficient	Reference to 25℃, I _D =-1mA		-0.03		V/°C
		V _{GS} =-10V , I _D =-12A		70	82	
RDS(ON)	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-8A		85	105	$\boldsymbol{m}\Omega$
V _G S(th)	Gate Threshold Voltage		-1.2	1.5	-2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	V_{GS} = V_{DS} , I_D =-250uA		4.56		mV/℃
		V _{DS} =-48V , V _{GS} =0V , T _J =25℃			1	
loss	Drain-Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =55℃			5	uA
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-12A		15.4		S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		13.5		Ω
Qg	Total Gate Charge (-4.5V)			9.86		
Q_{gs}	Gate-Source Charge	V _{DS} =-48V , V _{GS} =-4.5V , I _D =-10A		3.08		nC
Q_{gd}	Gate-Drain Charge			2.95		
Td(on)	Turn-On Delay Time			28.8		
Tr	Rise Time	V _{DD} =-15V , V _{GS} =-10V ,		19.8		ns
T _{d(off)}	Turn-Off Delay Time	- R _G =3.3□, I _D =-1A		60.8		
T _f	Fall Time			7.2		
Ciss	Input Capacitance			1447		
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		97.3		pF
Crss	Reverse Transfer Capacitance			70		
Is	Continuous Source Current ^{1,5}				-18	Α
Іѕм	Pulsed Source Current ^{2,5}	V _G =V _D =0V , Force Current			-36	Α
VsD	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25℃			-1.2	V

Note:

^{1.} The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

^{2.}The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%

^{3.} The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V, L=0.1mH, I_{AS} =-26.6A

^{4.} The power dissipation is limited by 150°C junction temperature

^{5.} The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.





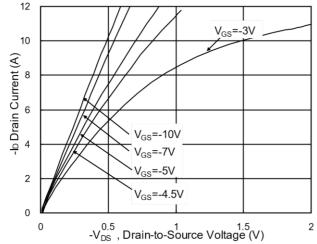


Fig.1 Typical Output Characteristics

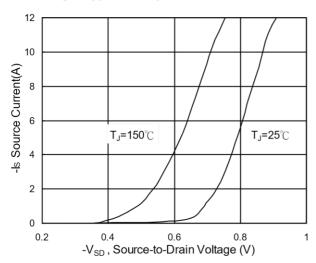


Fig.3 Forward Characteristics of Reverse

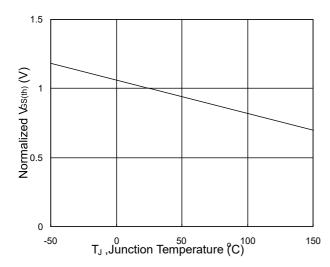


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

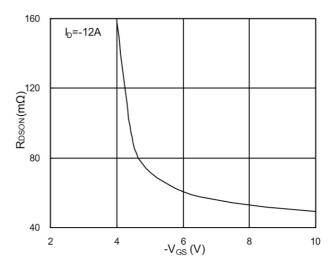


Fig.2 On-Resistance v.s Gate-Source

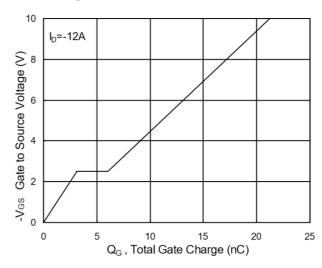


Fig.4 Gate-Charge Characteristics

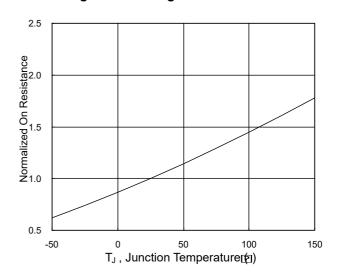
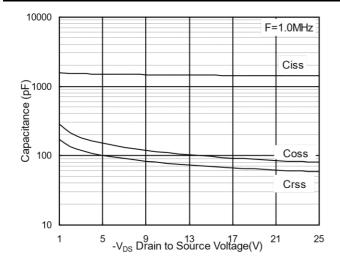


Fig.6 Normalized R_{DSON} v.s T_J



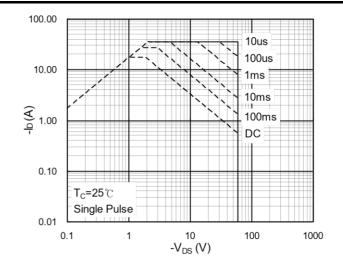


Fig.7 Capacitance

Fig.8 Safe Operating Area

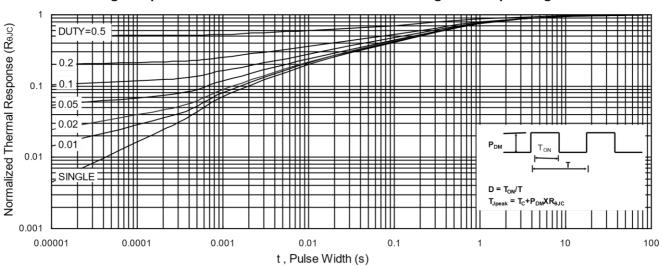


Fig.9 Normalized Maximum Transient Thermal Impedance

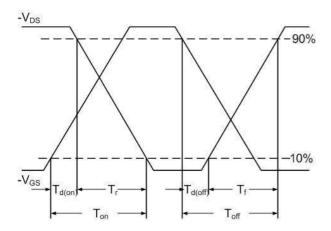


Fig.10 Switching Time Waveform

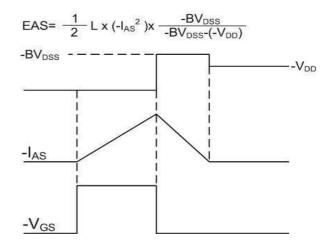
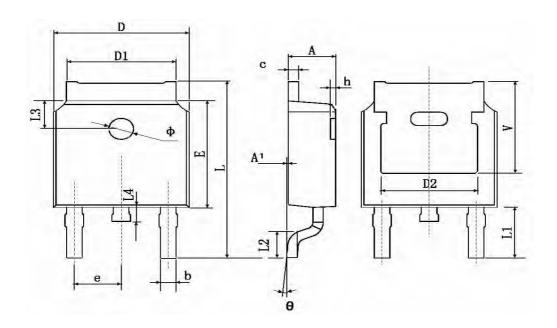


Fig.11 Unclamped Inductive Waveform



TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
A	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.83	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.90	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3	1.600 TYP.		0.063 TYP.			
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350 TYP.		0.211 TYP.			

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